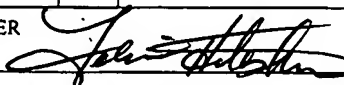


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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
A A	FH.	1	JP A 2003-002786 w/abst. & trans	01/08/2003	JAPAN	-	-
	FH.	2	JP A 08-268794 w/abst. & trans	10/15/1996	JAPAN	-	-
	FH.	3	JP A 08-330316 w/abst. & trans	12/13/1996	JAPAN	-	-
	FH.	4	JP A 2000-063196 w/abst. & trans	02/29/2000	JAPAN	-	-
	FH.	5	JP A 2000-313691 w/abst. & trans	11/14/2000	JAPAN	-	-
	FH.	6	JP A 2002-338389 w/abst. & trans	11/27/2002	JAPAN	-	-
	FH.	7	JP A 11-147786 w/abst. & trans	06/02/1999	JAPAN	-	-
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
FH.	8	V. V. Voronkov, "The mechanism of Swirl Defects formation in Silicon," Journal of Crystal Growth, 59 (1982), 625-643.					
FH.	9	F. Dupret et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No 9, pp. 1849-1871, 1990.					
EXAMINER				DATE CONSIDERED			
				6/22/2007			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: December 13, 2005